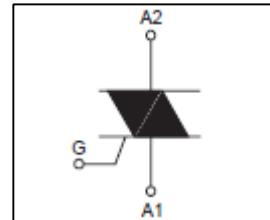


Features

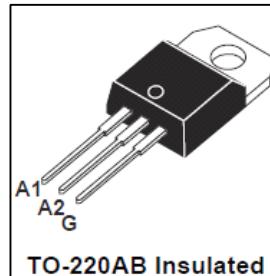
- Repetitive Peak off-State Voltage: 600V
- R.M.S On-State Current ($I_{T(RMS)}$) = 24A
- Low on-state voltage: $V_{TM} = 1.55V$ (Max.) @ $I_T = 11A$
- High Commutation dV/dt.

**General Description**

General purpose switching and phase control applications.

These devices are intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits such as fan speed and temperature modulation control, lighting control and static switching relay.

By using an internal ceramic pad, the WTPA series provides



Voltage insulated tab (rated at 2500V RMS)

Absolute Maximum Ratings (T_J=25°C unless otherwise specified)

Symbol	Parameter	Value	Units
V_{DRM}	Peak Repetitive Forward Blocking Voltage(gate open) (Note 1)	600	V
$I_{T(RMS)}$	Forward Current RMS (All Conduction Angles, T _c =58°C)	24	A
I_{TSM}	Peak Forward Surge Current, (1/2 Cycle, Sine Wave, 50/60 Hz)	250/260	A
I^2t	Circuit Fusing Considerations (t p= 10 ms)	340	A ² s
P_{GM}	Peak Gate Power — Forward, (T _c = 58°C, Pulse width ≤ 1.0μs)	5	W
$P_{G(AV)}$	Average Gate Power — Forward, (Over any 20ms period)	1	W
I_{FGM}	Peak Gate Current — Forward, T _j = 125°C (20 μs, 120 PPS)	4	A
V_{RGM}	Peak Gate Voltage — Reverse, T _j = 125°C (20 μs, 120 PPS)	10	V
T _J	Junction Temperature	-40~125	°C
T _{stg}	Storage Temperature	-40~150	°C

Note1: Although not recommended, off-state voltages up to 800V may be applied without damage, but the TRIAC may switch to the on-state. The rate of rise of current should not exceed 3A/us.

Thermal Characteristics

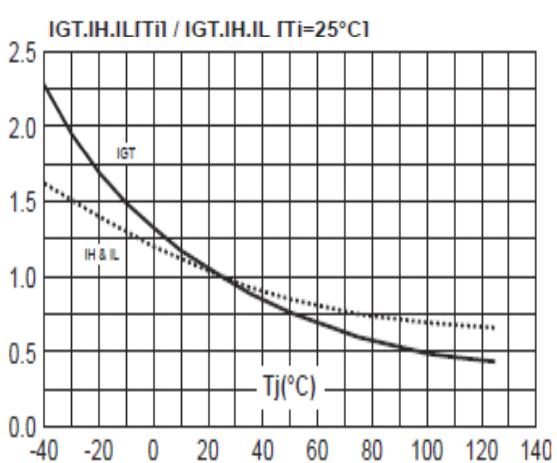
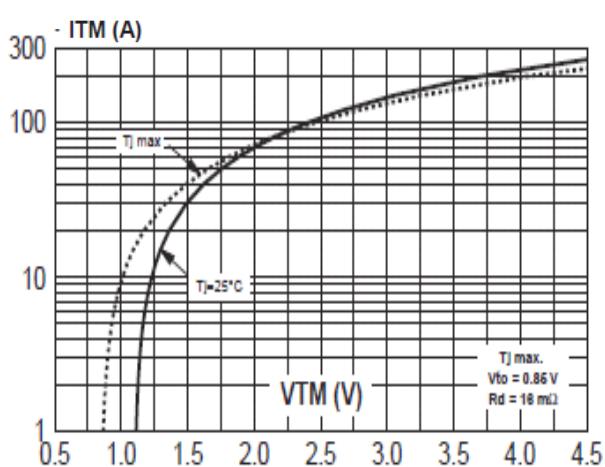
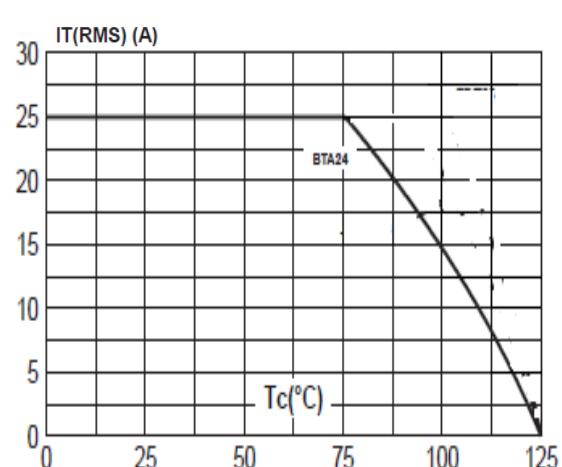
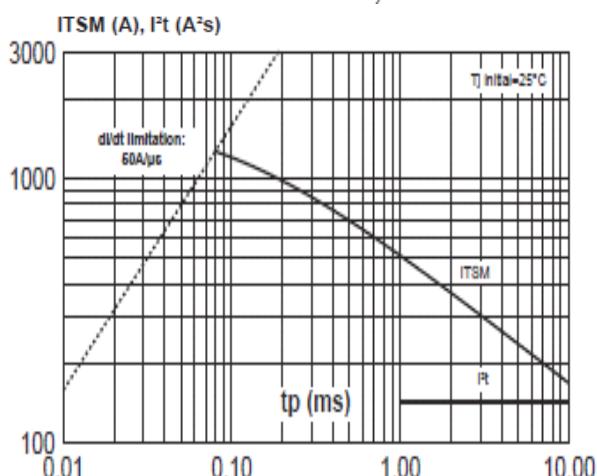
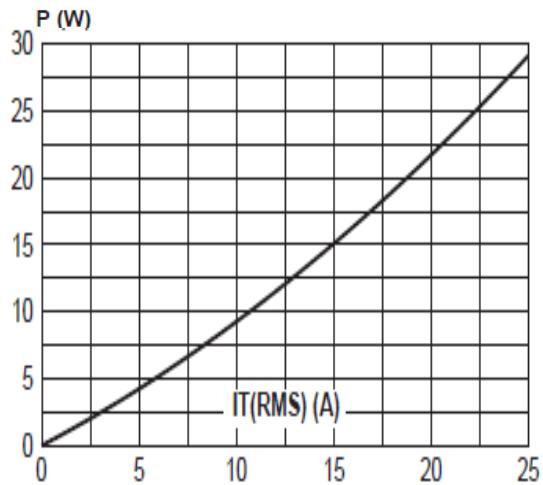
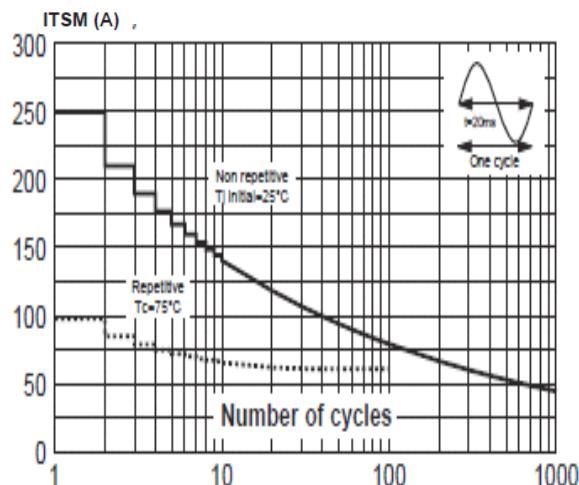
Symbol	Parameter	Value			Units
		Min	Typ	Max	
R _{QJC}	Thermal Resistance, Junction-to-Case	-	-	1.7	°C/W
R _{QJA}	Thermal Resistance, Junction-to-Ambient	-	-	60	°C/W

WTPA24A60BW

Electrical Characteristics (Tc = 25°C unless otherwise specified)

Symbol	Characteristics		Min	Typ.	Max	Unit
I _{DRM} /I _{RRM}	Peak Forward or Reverse Blocking Current (V _{DRM} =V _{RRM})	Tc=25°C	-	-	5	µA
		Tc=125°C	-	-	3	mA
V _{TM}	Forward "On" Voltage(Note2) (I _{TM} = 35A Peak @ TA = 25°C)		-	-	1.55	V
I _{GT}	Gate Trigger Current (Continuous dc) (V _D = 12 Vdc, RL = 33Ω)	T2+G+	-	-	50	mA
		T2+G-	-	-	50	
		T2-G-	-	-	50	
V _{GT}	Gate Trigger Voltage (Continuous dc) (V _D = 12 Vdc, RL = 33Ω)	T2+G+	-	-	1.2	V
		T2+G-	-	-	1.2	
		T2-G-	-	-	1.2	
V _{GD}	Gate threshold voltage(Tj=125°C, V _D = V _{DRM} , RL = 3.3kΩ)	0.2	-	-	-	V
dV/dt	Critical rate of rise of commutation Voltage (V _D =0.67V _{DRM})	1000	-	-	-	V/µs
dI _{com} /dt	Critical rate of rise On-State voltage(V _D =400V, Tj=125°C)	22	-	-	-	A/µs
I _H	Holding Current (I _T = 500 mA)	-	-	80	-	mA
I _L	I _G =1.2I _{GT}	-	-	100	-	mA
R _d	Dynamic resistance	-	-	16	-	mΩ

Note 2. Forward current applied for 1 ms maximum duration, duty cycle



WTPA24A60BW

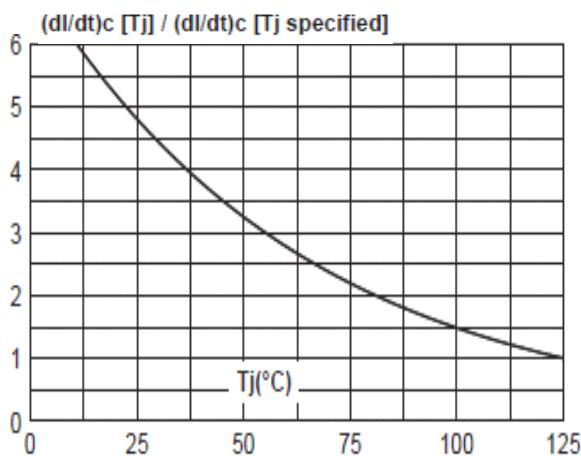


Fig.7 : Relative variation of critical rate of decrease of main current versus junction temperature.

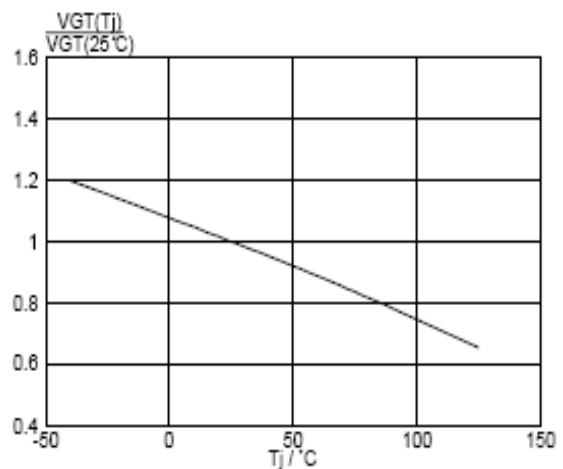


Fig.8 Normalised gate trigger voltage $V_{GT}(T_j) / V_{GT}(25^\circ\text{C})$, versus junction temperature T_j .

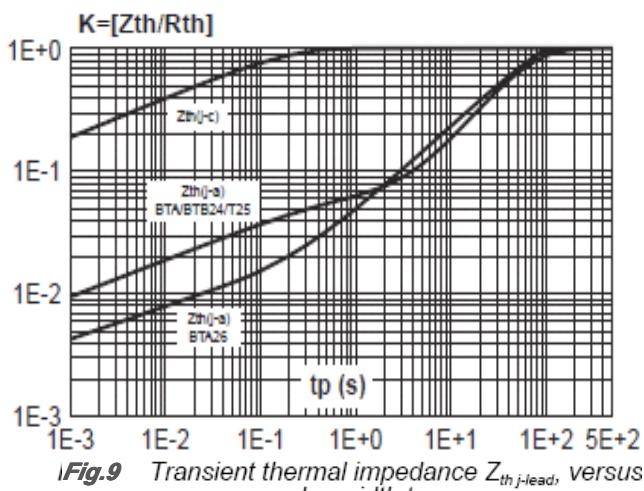


Fig.9 Transient thermal impedance $Z_{th,j-lead}$, versus pulse width t_p .

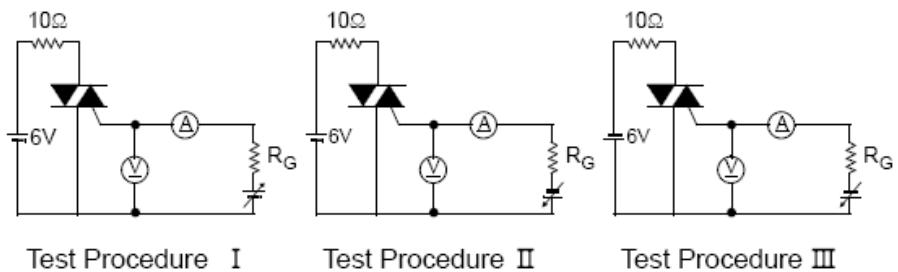


Fig.10 Gate Trigger Characteristics Test Circuit

TO-220 Package Dimension